N-Channl Silicon MOSFET

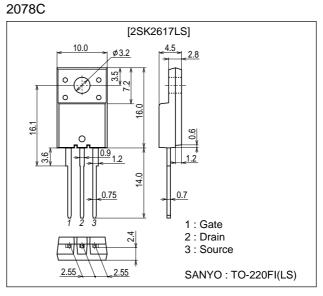


Features

- Low ON-resistance.
- Low Qg.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|-----------------------------|--------|------------|-------------|------|
| Drain-to-Source Voltage | VDSS | | 500 | V |
| Gate-to-Source Voltage | VGSS | | ±30 | V |
| Drain Current (DC) | ١D | | 4 | А |
| Drain Current (Pulse) | IDP | | 16 | А |
| Allowable Power Dissipation | PD | | 2.0 | W |
| | PD | Tc=25°C | 25 | W |
| Channel Temperature | Tch | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Electrical Characteristics at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|---------------------------------------|----------|---|---------|-----|------|------|
| | | | min | typ | max | Unit |
| Drain-to-Source Breakdown Voltage | V(BR)DSS | ID=1mA, VGS=0 | 500 | | | V |
| Zero-Gate Voltage Drain Current | IDSS | V _{DS} =500V, V _{GS} =0 | | | 1.0 | mA |
| Gate-to-Source Leakage Current | IGSS | VGS=±30V, VDS=0 | | | ±100 | nA |
| Cutoff Voltage | VGS(off) | V _{DS} =10V, I _D =1mA | 3.5 | | 5.5 | V |
| Forward Transfer Admittance | yfs | V _{DS} =10V, I _D =2A | 1.1 | 2.2 | | S |
| Marking : K2617 Continued on next pag | | | | | | |

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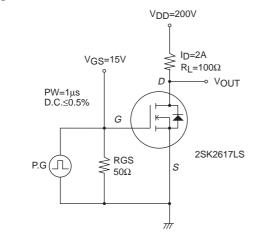
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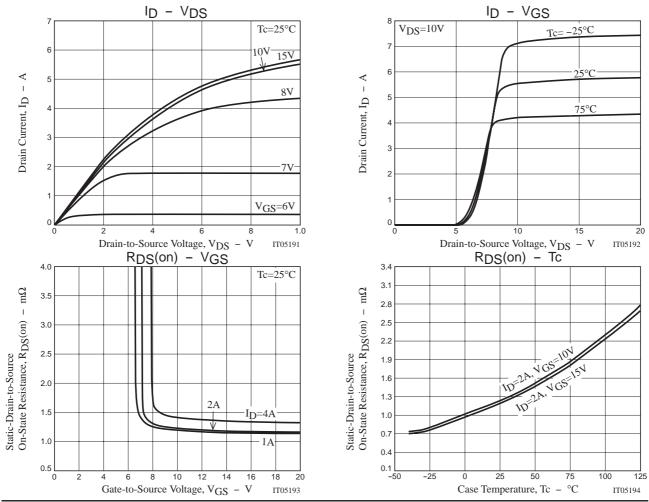
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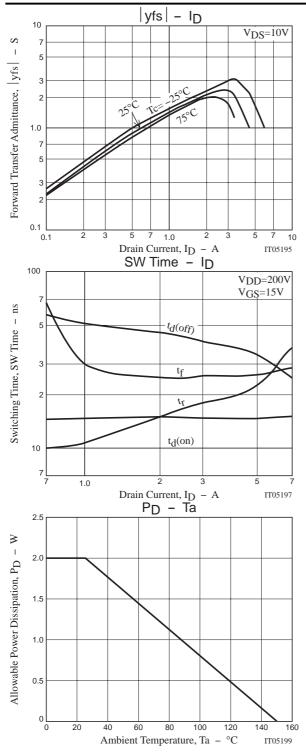
| Parameter | Symbol | Conditions | Ratings | | | - Unit |
|--|----------------------|---|---------|------|-----|--------|
| | | | min | typ | max | Unit |
| Static Drain-to-Source On-State Resistance | R _{DS} (on) | ID=2A, VGS=15V | | 1.2 | 1.6 | Ω |
| Input Capacitance | Ciss | V _{DS} =20V, f=1MHz | | 550 | | pF |
| Output Capacitance | Coss | V _{DS} =20V, f=1MHz | | 190 | | pF |
| Reverse Transfer Capacitance | Crss | V _{DS} =20V, f=1MHz | | 95 | | pF |
| Total Gate Charge | Qg | V _{DS} =200V, I _D =4A, V _{GS} =10V | | 15 | | nC |
| Turn-ON Delay Time | t _d (on) | See specified Test Circuit. | | 15 | | ns |
| Rise Time | tr | See specified Test Circuit. | | 15 | | ns |
| Turn-OFF Delay Time | t _d (off) | See specified Test Circuit. | | 45 | | ns |
| Fall Time | tf | See specified Test Circuit. | | 25 | | ns |
| Diode Forward Voltage | V _{SD} | IS=4A, VGS=0 | | 0.95 | 1.2 | V |

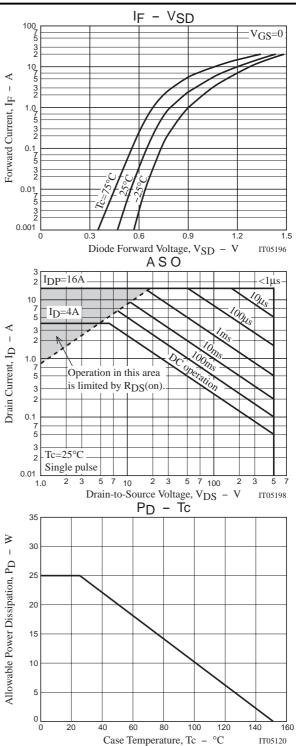
Switching Time Test Circuit





No.5443-2/4





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